

10-639,465

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)		APPLICANT YAMAZAKI, et al.	
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
GA	AA 6,200,866	3-2001	Ma, et al.			
	AB 6,319,840	11-2001	Costrini, et al.			
	AC 6,335,266	1-2002	Kitahara, et al.			
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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation
GA	AM 11330463	11-1999	Japan			
GA	AN 2805924	9-2001	France			
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GA	AU	Polysilicon-Germanium Gate Patterning Studies in a High Density Plasma Helicon Source, 1997 American Vacuum Society, pp. 1874-1880
GA	AV	Germanium Etching in High Density Plasmas for 0.18 PM Complementary Metal-Oxide-Semiconductor Gate Patterning Applications, 1998 American Vacuum Society, pp. 1833-1840
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Examiner George Goudreau		Date Considered 3-06'